

2N6430 2N6431 NPN
2N6432 2N6433 PNP

**COMPLEMENTARY
SILICON TRANSISTORS**



TO-18 CASE



www.centrasemi.com

DESCRIPTION:

The CENTRAL SEMICONDUCTOR 2N6430 series devices are complementary small signal silicon transistors manufactured by the epitaxial planar process, designed for high voltage amplifier applications.

MARKING: FULL PART NUMBER

MAXIMUM RATINGS: ($T_A=25^\circ\text{C}$ unless otherwise noted)

SYMBOL	2N6430	2N6431	UNITS
	2N6432	2N6433	
Collector-Base Voltage	V_{CBO} 200	300	V
Collector-Emitter Voltage	V_{CEO} 200	300	V
Emitter-Base Voltage (NPN)	V_{EBO}	6.0	V
Emitter-Base Voltage (PNP)	V_{EBO}	5.0	V
Continuous Collector Current	I_C	500	mA
Power Dissipation ($T_C=25^\circ\text{C}$)	P_D	1.8	W
Power Dissipation	P_D	500	mW
Operating and Storage Junction Temperature	T_J, T_{stg}	-65 to +200	$^\circ\text{C}$
Thermal Resistance	θ_{JA}	0.35	$^\circ\text{C}/\text{mW}$
Thermal Resistance	θ_{JC}	97.2	$^\circ\text{C}/\text{W}$

ELECTRICAL CHARACTERISTICS: ($T_A=25^\circ\text{C}$)

SYMBOL	TEST CONDITIONS	2N6430		2N6432		UNITS
		2N6431	2N6433	MIN	MAX	
I_{CBO}	$V_{CB}=160\text{V}$ (2N6430, 2N6432)	-	100	-	250	nA
I_{CBO}	$V_{CB}=200\text{V}$ (2N6431, 2N6433)	-	100	-	250	nA
I_{EBO}	$V_{EB}=4.0\text{V}$	-	100	-	-	nA
I_{EBO}	$V_{EB}=3.0\text{V}$	-	-	-	100	nA
BV_{CBO}	$I_C=100\mu\text{A}$ (2N6430, 2N6432)	200	-	200	-	V
BV_{CBO}	$I_C=100\mu\text{A}$ (2N6431, 2N6433)	300	-	300	-	V
BV_{CEO}	$I_C=1.0\text{mA}$ (2N6430, 2N6432)	200	-	200	-	V
BV_{CEO}	$I_C=1.0\text{mA}$ (2N6431, 2N6433)	300	-	300	-	V
BV_{EBO}	$I_E=100\mu\text{A}$	6.0	-	5.0	-	V
$V_{CE(SAT)}$	$I_C=20\text{mA}, I_B=2.0\text{mA}$	-	0.5	-	0.5	V
$V_{BE(SAT)}$	$I_C=20\text{mA}, I_B=2.0\text{mA}$	-	0.9	-	0.9	V
h_{FE}	$V_{CE}=10\text{V}, I_C=1.0\text{mA}$	25	-	25	-	
h_{FE}	$V_{CE}=10\text{V}, I_C=10\text{mA}$	40	-	40	-	
h_{FE}	$V_{CE}=10\text{V}, I_C=30\text{mA}$	50	200	30	150	

R2 (3-April 2018)

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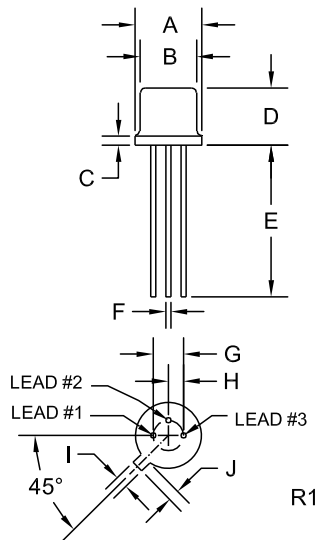
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ELECTRICAL CHARACTERISTICS - Continued: ($T_A=25^\circ\text{C}$)

SYMBOL	TEST CONDITIONS	2N6430 2N6431		2N6432 2N6433		UNITS
		MIN	MAX	MIN	MAX	
f_T	$V_{CE}=20\text{V}$, $I_C=10\text{mA}$, $f=100\text{MHz}$	50	200	-	-	MHz
f_T	$V_{CE}=20\text{V}$, $I_C=10\text{mA}$, $f=20\text{MHz}$	-	-	50	-	MHz
C_{ob}	$V_{CB}=20\text{V}$, $I_E=0$, $f=1.0\text{MHz}$	-	4.0	-	6.0	pF

TO-18 CASE - MECHANICAL OUTLINE



SYMBOL	DIMENSIONS			
	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A (DIA)	0.209	0.230	5.31	5.84
B (DIA)	0.178	0.195	4.52	4.95
C	-	0.030	-	0.76
D	0.170	0.210	4.32	5.33
E	0.500	-	12.70	-
F (DIA)	0.016	0.019	0.41	0.48
G (DIA)	0.100		2.54	
H	0.050		1.27	
I	0.036	0.046	0.91	1.17
J	0.028	0.048	0.71	1.22

TO-18 (REV: R1)

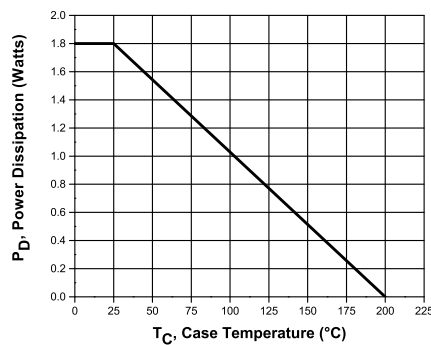
LEAD CODE:

- 1) Emitter
- 2) Base
- 3) Collector

MARKING:

FULL PART NUMBER

Power Derating



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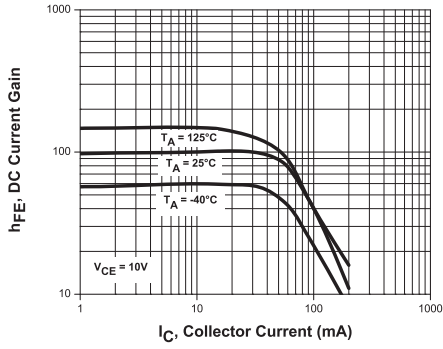
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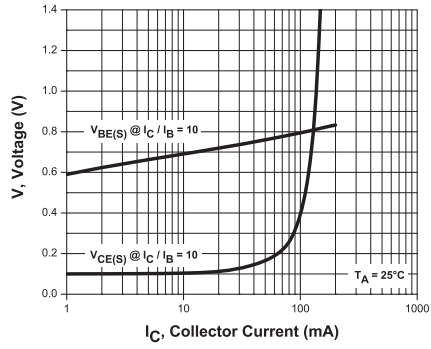


NPN TYPICAL ELECTRICAL CHARACTERISTICS

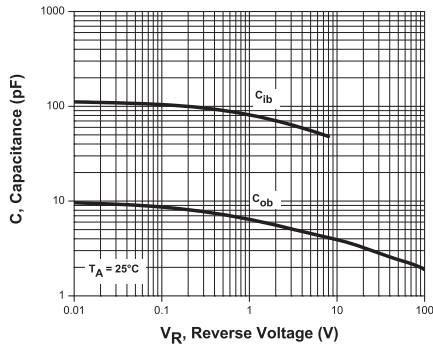
DC Current Gain



"ON" Voltage



Capacitance



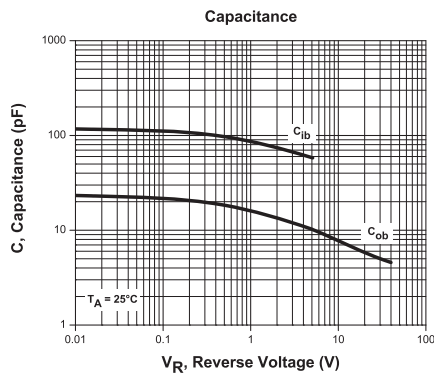
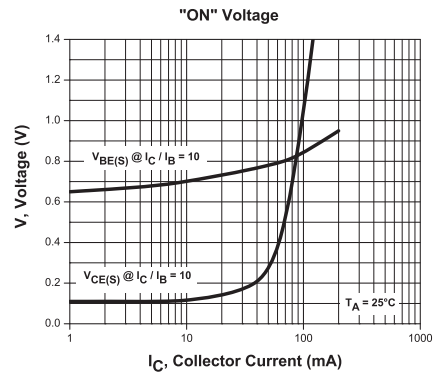
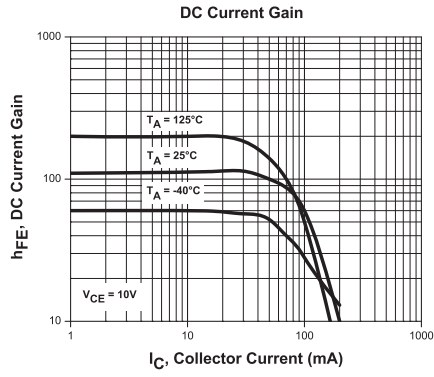
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PNP TYPICAL ELECTRICAL CHARACTERISTICS



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